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## Correction: High-k double gate junctionless tunnel FET with a tunable bandgap

Shiromani Balmukund Rahi<sup>\*a</sup> and Bahniman Ghosh<sup>b</sup>

Correction for 'High-k double gate junctionless tunnel FET with a tunable bandgap' by Shiromani Balmukund Rahi *et al.*, *RSC Adv.*, 2015, 5, 54544–54550.

The authors apologise for the errors in eqn (3). The correct equation is as follows:

$$E_g^{\text{SiGe}} = 1.084 - 0.42x \quad (3)$$

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

<sup>a</sup>Department of Electrical Engineering, Indian Institute of Technology Kanpur, Kanpur-208016, India. E-mail: [sbrahi@iitk.ac.in](mailto:sbrahi@iitk.ac.in)

<sup>b</sup>Microelectronics Research Center, University of Texas at Austin, Austin-78758, USA. E-mail: [bghosh@utexas.edu](mailto:bghosh@utexas.edu)

